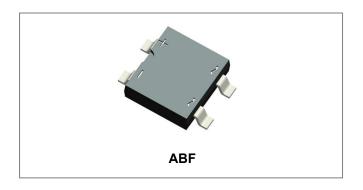


ABF2U THRU ABF10U

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RoHS HF

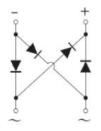
ABF2U THRU ABF10U SINGLE PHASE 1.0AMP SURFACE MOUNT GLASS PASSIVATED BRIDGE RECTIFIER



Features

- Glass passivated die construction
- Low forward voltage drop
- High current capability
- High surge current capability
- Designed for surface mount application
- Plastic material-UL flammability 94V-0
- This is a Halogen Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram



Mechanical Data

- Case: SOPA-4, Molded plastic ABF
- Terminals: Plated leads solderable per MIL-STD-202, Method 208
- Polarity: Polarity symbols marked on case
- Mounting Position: Any

Maximum Ratings@T_A=25°C unless otherwise specified

Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

Characteristic	Symbol	ABF2U	ABF4U	ABF6U	ABF8U	ABF10U	Units
Maximum repetitive peak reverse voltage	V _{RRM}	200	400	600	800	1000	
RMS Reverse Voltage	V _{R(RMS)}	140	280	420	560	700	V
Maximum DC blocking voltage	V _{DC}	200	400	600	800	1000	
Average Rectified Output Current @T _c = 100°C	I _{F(AV)}	1.0			V		
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	35				А	
Rating for fusing (t<8.3ms)	l²t	5.08				A ² s	

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Electrical Characteristics:

Characteristic	Symbol	ABF2U	ABF4U	ABF6U	ABF8U	ABF10U	Units
Forward voltage per element @ $I_F = 0.5A$ @ $I_F = 1.0A$	VF			0.95 1.0			V
Maximum DC reverse current $T_A = 25^{\circ}C$ at rated DC blocking voltage $T_A = 125^{\circ}C$	IR	5 200			μA		

* Pulse width < 300 μ s, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristic	Symbol	ABF2U	ABF4U	ABF6U	ABF8U	ABF10U	Units
Typical thermal resistance per leg (Note 1)	$R_{ extsf{ heta}JL}$ $R_{ extsf{ heta}JA}$	62.5 25		°C/W			
Operating and storage temperature range	TJ,TSTG	-55 to +150		°C			

Note: 1. Thermal resistance form junction to ambient and junction to lead mounted on P.C.B. with 0.2X0.2"(5X5mm) copper pads.

Ratings and Characteristics Curves

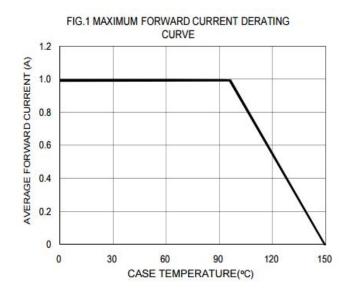
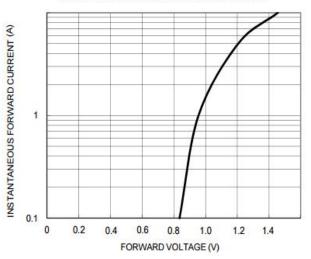


FIG. 2 TYPICAL FORWARD CHARACTERISTIC





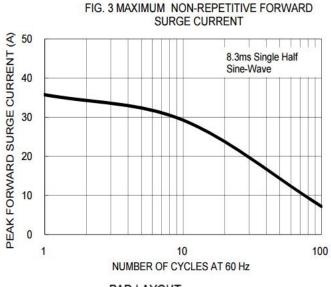
RoHS HF



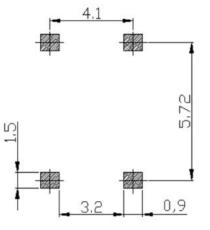
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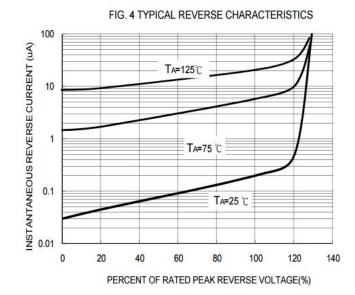
ABF2U THRU ABF10U

RoHS HF







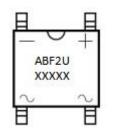


Ordering Information

Device	Package	Shipping
ABF2U THRU ABF10U	ABF	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

ABF2U	= Type Numbe
	1

= Year = Week

YΥ

WW

Т

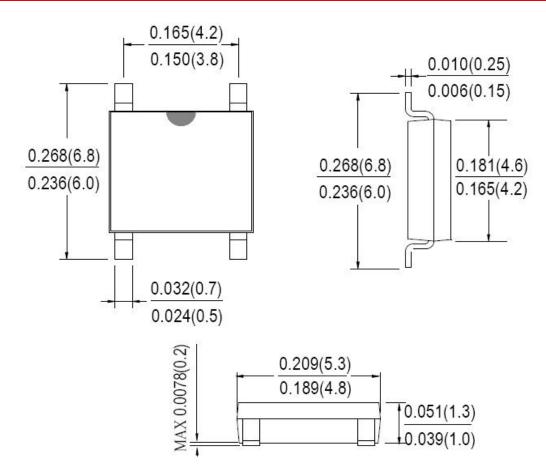
= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

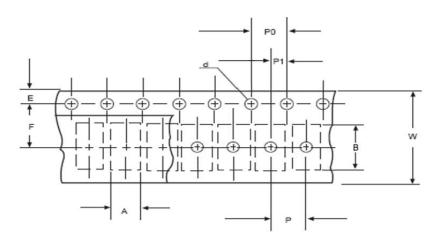
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Mechanical Dimensions ABF(Inches/Millimeters)



Carrier Tape & Reel Specification ABF



SYMBOL	Millimeters				
STMBOL	Min.	Max.			
A	5.00	5.40			
В	6.40	6.80			
d	1.40	1.60			
E	1.40	1.60			
F	5.55	5.75			
Р	3.90	4.10			
P0	3.90	4.10			
P1	1.90	2.10			
W	11.50	12.50			

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